



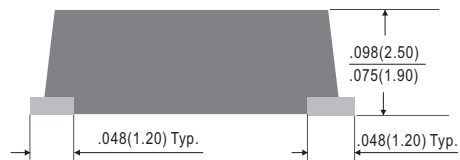
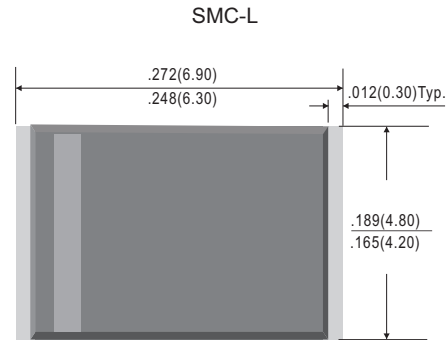
Features

- Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance.
- Low profile surface mounted application in order to optimize board space.
- High current capability.
- Superfast recovery time for switching mode application.
- High surge current capability.
- Glass passivated chip junction.
- **Moisture Sensitivity Level 1**

Mechanical data

- Epoxy:UL94-V0 rated flame retardant
- Case : Molded plastic, DO-214AB / SMC
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity : Indicated by cathode band
- Mounting Position : Any
- Weight : Approximated 0.19 gram

Package outline



Dimensions in inches and (millimeters)

Maximum ratings and Electrical Characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	See Fig.2	I_o			3.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	I_{FSM}			100	A
Reverse current	$V_R = V_{RRM} \quad T_J = 25^\circ\text{C}$	I_R			5.0	μA
	$V_R = V_{RRM} \quad T_J = 125^\circ\text{C}$				100	
Diode junction capacitance	f=1MHz and applied 4V DC reverse voltage	C_j		45		pF
Storage temperature		T_{STG}	-55		+150	$^\circ\text{C}$

SYMBOLS	V_{RRM}^{*1} (V)	V_{RMS}^{*2} (V)	V_R^{*3} (V)	V_F^{*4} (V)	t_{rr}^{*5} (ns)	Operating temperature $T_J, (^\circ\text{C})$
SFM31L	50	35	50	0.95	35	-55 to +150
SFM32L	100	70	100			
SFM34L	200	140	200			
SFM36L	400	280	400	1.25		
SFM38L	600	420	600	1.70		

- *1 Repetitive peak reverse voltage
- *2 RMS voltage
- *3 Continuous reverse voltage
- *4 Maximum forward voltage@ $I_F=3.0\text{A}$
- *5 Maximum Reverse recovery time, note 1

Note 1. Reverse recovery time test condition, $I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$



Rating and characteristic curves

FIG.1-TYPICAL FORWARD CHARACTERISTICS

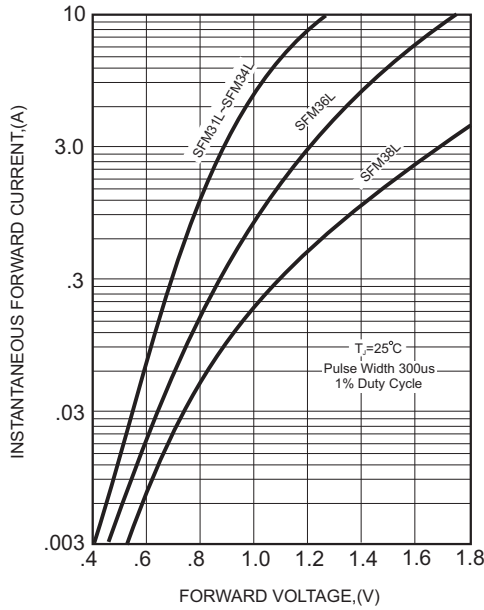


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

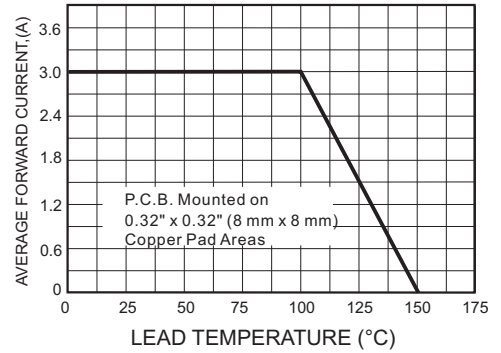


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

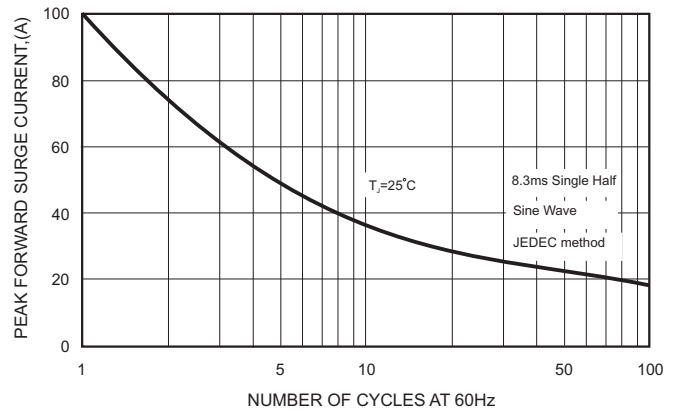
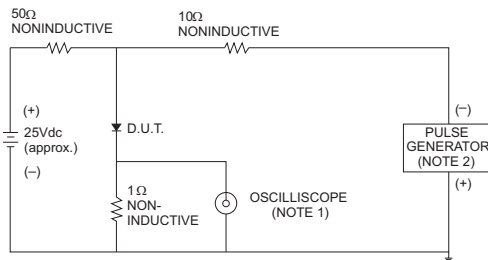


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

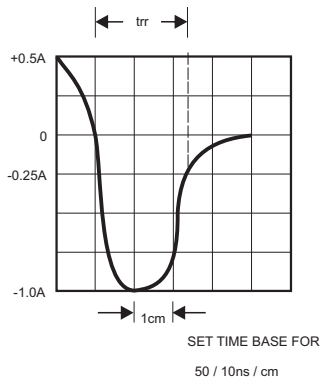
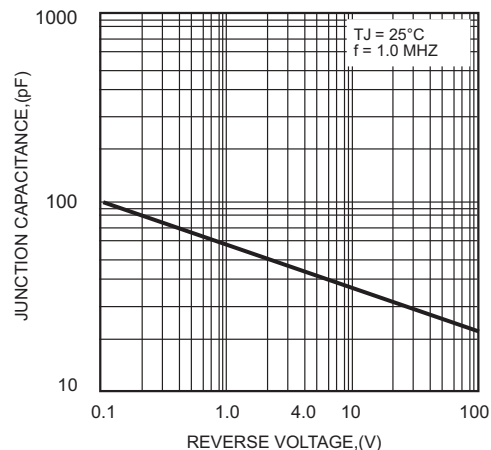


FIG.5-TYPICAL JUNCTION CAPACITANCE





Pinning information

Pin	Simplified outline	Symbol
Pin1 cathode Pin2 anode		

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA. (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SMC-L	13"	3,000	8.0	6,000	337*337*37	330	350*330*360	48,000	17.2

Marking

Type number	Marking code
SFM31L-TH	S31
SFM32L-TH	S32
SFM34L-TH	S34
SFM36L-TH	S36
SFM38L-TH	S38

Note: L: Package code, SMC-L

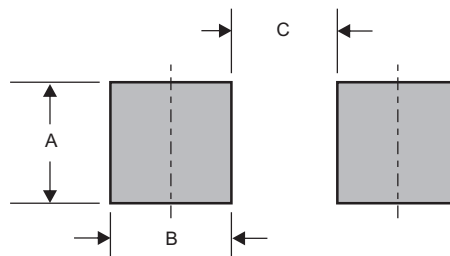
-T: Taping Reel

Pb-Free package is available

RoHS product for packing code suffix "G"

Halogen free product for packing code suffix "H"

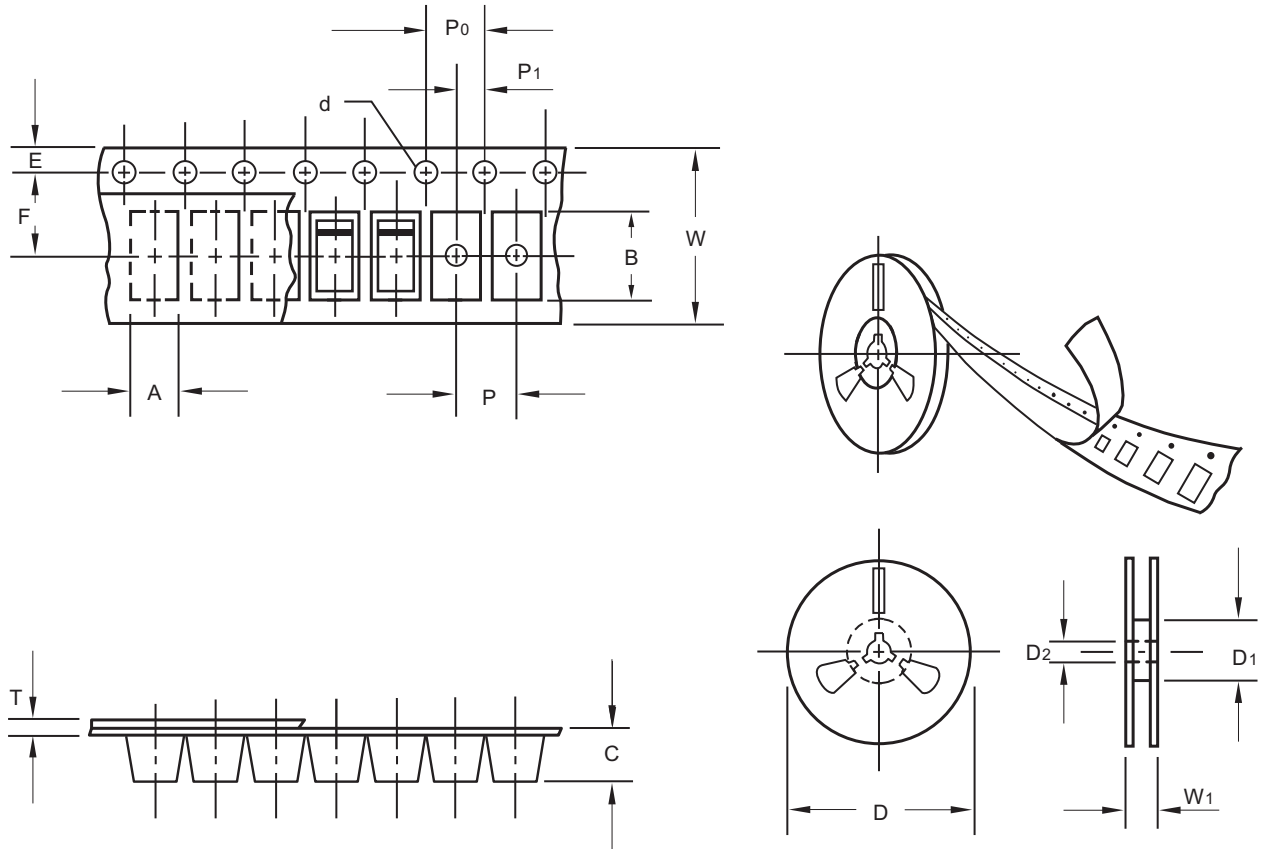
Suggested solder pad layout



Dimensions in inches and (millimeters)

PACKAGE	A	B	C
SMC-L	0.189 (4.80)	0.063 (1.60)	0.158 (4.00)

Packing information



unit:mm

Item	Symbol	Tolerance	SMC-L
Carrier width	A	0.1	5.10
Carrier length	B	0.1	7.20
Carrier depth	C	0.1	2.50
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	330.00
13" Reel inner diameter	D1	min	50.00
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	5.50
Punch hole pitch	P	0.1	8.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	12.00
Reel width	W1	1.0	18.00

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.